

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-18 (canceled)

19. (new) A method for cleaning of an integrated circuit substrate, which comprises: removing the residue by a sequential application on the substrate of (a) a first aqueous composition comprising hydrogen fluoride, followed by (b) a second composition comprising a mixture of hydrogen peroxide with a compound selected from the group consisting of ammonium hydroxide, hydrochloric acid and sulfuric acid, wherein (i) said application occurs at a temperature from about 15° C to about 90° C, (ii) said application further comprises megasonic physical cleaning, and (iii) the integrated surface substrate has thereon a residue of by-products of a high-k dielectric etch process.

20. (new) The method as recited in claim 19, wherein the application comprises from about 0.05 to about 30 percent of hydrogen fluoride based on the volume of the application.

21. (new) The method as recited in claim 20, wherein the application further includes ammonium hydroxide

22. (new) The method as recited in claim 21, wherein the application comprises from about 0.05 to about 30 percent of hydrogen peroxide based on the volume of the application.

23. (new) The method as recited in claim 19, wherein said cleaning comprises contacting the integrated circuit substrate with the application for about 10 seconds to about 10 minutes.

24. (new) A method for cleaning of an integrated circuit substrate, which consists essentially of:

removing the residue by a sequential application on the substrate of (a) a first aqueous composition of hydrogen fluoride, followed by (b) a second composition of a mixture of hydrogen peroxide with a compound selected from the group consisting of ammonium hydroxide, hydrochloric acid and sulfuric acid, wherein (i) said application occurs at a temperature from about 15° C to about 90° C, (ii) the application includes from about 0.05 to about 30 percent of hydrogen fluoride based on the volume of the application, and (iii) the integrated surface substrate has thereon a residue of by-products of a high-k dielectric etch process.

25. (new) The method as recited in claim 24, wherein the application further includes ammonium hydroxide.

26. (new) The method as recited in claim 25, wherein the application further includes from about 0.05 to about 30 percent of hydrogen peroxide based on the volume of the application.

27. (new) The method as recited in claim 24, wherein said cleaning includes contacting the integrated circuit substrate with the application for about 10 seconds to about 10 minutes.

28. (new) The method as recited in claim 27, wherein said cleaning further includes megasonic physical cleaning.

29. (new) A method for cleaning of an integrated circuit substrate, which consists essentially of:
removing the residue by a sequential application on the substrate of (a) a first aqueous composition of hydrogen fluoride, followed by (b) a second composition of a mixture of hydrogen peroxide with a compound selected from the group consisting of ammonium hydroxide, hydrochloric acid and sulfuric acid, wherein (i) said application occurs at a temperature from about 15° C to about 90° C, (ii) the application includes from about 0.05 to about 30 percent of hydrogen peroxide, based on the volume of the application, and (iii) the

integrated surface substrate has thereon a residue of by-products of a high-k dielectric etch process.

30. (new) The method as recited in claim 29, wherein the application further includes from about 0.05 to about 30 percent of hydrogen fluoride based on the volume of the application.

31. (new) The method as recited in claim 29, wherein the application further includes ammonium hydroxide.

32. (new) The method as recited in claim 29, wherein said cleaning includes contacting the integrated circuit substrate with the application for about 10 seconds to about 10 minutes.

33. (new) The method as recited in claim 32, wherein said cleaning further includes megasonic physical cleaning.